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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q61744

Hisayuki MIKI, et al.

Appln. No.: 09/900,962

Group Art Unit: 2812

Confirmation No.: 7972

Examiner: Savitri Mulpuri

Filed: July 10, 2001

For: METHOD FOR PRODUCING P-TYPE GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR, METHOD FOR PRODUCING GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

This Amendment is submitted in response to the Office Action dated November 15, 2002, in which the Examiner set a three-month period for response. Review and reconsideration on the merits in view of the following remarks and amendments is respectfully requested.

Please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 1-7 and 14 without prejudice or disclaimer.

Please enter the following amended claims:

8. (Amended) A method for producing a gallium nitride-based compound semiconductor light-emitting device comprising providing an n-type layer and a light-emitting layer each comprising a gallium nitride-based compound semiconductor, providing a p-type layer comprising a gallium nitride-based compound semiconductor through the following steps: